

Call for Papers Issued for 9th Oxford Conference on Microscopy of Semiconducting Materials

The ninth in the series of biennial conferences on Microscopy of Semiconducting Materials will be held at Oxford University, March 20–23, 1995. The conference will focus on the latest developments in transmission and scanning electron microscopy studies of the structural and electrical properties of semiconductors. Recent advances in using other micro-characterization techniques such as x-ray topography, scanning probe microscopy, and atom probe microanalysis will also be featured. Materials of interest cover the complete range of elemental and compound semiconductors.

The state-of-the-art in a number of subject areas will be addressed, including the characterization of as-grown semiconductors in both bulk and thin film forms, the study of lattice defect and impurity behavior and the investigation of the effects of advanced semiconductor processing procedures. Special conference sessions will concentrate on recent developments in high-resolution electron microscopy, scanning probe microscopy, the properties of dislocations, the characteristics of epitaxial layers, quantum wells

and superlattices, the nature of metal-semiconductor contacts and silicides and the effects of device processing treatments.

Invited speakers and their topics provisionally include:

- V.V. Aristov (Microelectronics Technology Institute, Chernogolovka), "SEM of Multilayers";
- G.R. Booker (University of Oxford), "Scanning IR Microscopy Applications";
- D.J. Eaglesham (AT&T Bell Labs, Murray Hill, NJ), "Si Processing Phenomena";
- D. Gerthsen (University of Karlsruhe), "Epitaxial Growth Mechanisms";
- K. Ishida (NEC, Kanagawa), "HREM of Interfaces";
- D.D. Perovic (University of Toronto), "Dislocations in Epitaxial Systems";
- P. Pirouz (Case Western Reserve University, Cleveland, OH), "New Aspects of Dislocation Phenomena";
- A. Rocher (CEMES, Toulouse), "Heterostructure Relaxation";
- G.A. Rozgonyi (North Carolina State University, Raleigh, NC), "Silicides for Giga-Scale ICs";
- G. Salviati (MASPEC-CNR, Parma),

"TEM and XRD of Multilayers"; M.E. Welland (University of Cambridge), "Advances in SPM Applications"; and C.R. Whitehouse (University of Sheffield), "Real-Time Synchrotron X-Ray Studies of Epitaxy."

The conference proceedings will be published and contributed papers are requested in all the areas outlined above. For further details about the scientific program, please contact: 9th Oxford Conference Co-Chairman, A.G. Cullis, DRA Malvern, St. Andrews Road, Malvern, Worcs. WR14 3PS, United Kingdom (44-684-894509; fax 44-684-894311). For information about abstract submission (deadline **December 1, 1994**) and registration, contact: Meetings and Conferences, The Institute of Physics, 47 Belgrave Square, London SW1X 8QX, United Kingdom, 44-71-235-6111; fax 44-71-823-1051).

This conference is organized with the sponsorship of the U.K. Institute of Physics and the Royal Microscopical Society, and is endorsed by the Materials Research Society.

NOTE: See p. 69 in this issue for information about calls from North America to the United Kingdom. □

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